Switching Transistors

NPN Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	15	Vdc
Collector – Emitter Voltage	V _{CES}	40	Vdc
Collector – Base Voltage	V _{CBO}	40	Vdc
Emitter-Base Voltage	V _{EBO}	4.5	Vdc
Collector Current – Continuous	Ι _C	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

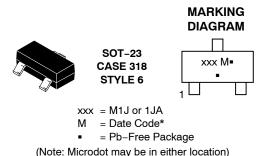
1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.

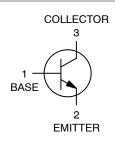


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*Date Code orientation and/or overbar may vary depending upon manufacturing location.



ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT2369LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT2369LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBT2369LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT2369ALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBT2369ALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

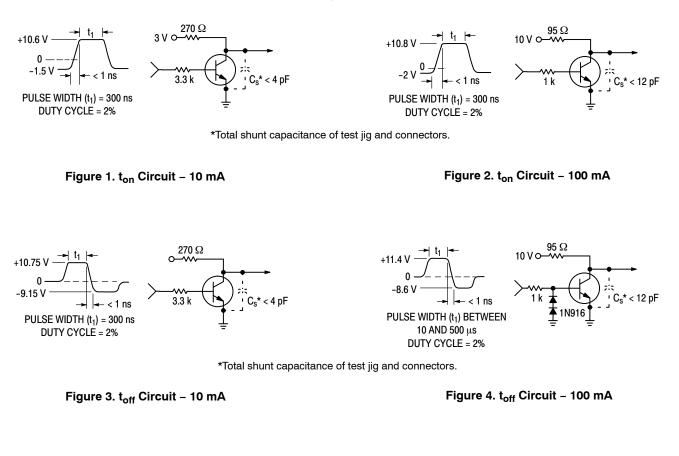
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 3) ($I_C = 10 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	15	-	_	Vdc
Collector – Emitter Breakdown Voltage $(I_C = 10 \ \mu Adc, \ V_{BE} = 0)$	V _{(BR)CES}	40	-	_	Vdc
Collector – Base Breakdown Voltage $(I_C = 10 \ \mu Adc, I_E = 0)$	V _{(BR)CBO}	40	-	_	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \ \mu Adc, I_C = 0$)	V _{(BR)EBO}	4.5	_	_	Vdc
Collector Cutoff Current ($V_{CB} = 20 \text{ Vdc}, I_E = 0$) ($V_{CB} = 20 \text{ Vdc}, I_E = 0, T_A = 150^{\circ}\text{C}$)	I _{СВО}			0.4 30	μAdc
Collector Cutoff Current MMBT2369A (V _{CE} = 20 Vdc, V _{BE} = 0)	I _{CES}	-	_	0.4	μAdc
ON CHARACTERISTICS		•	•	•	
$\begin{array}{l} \text{DC Current Gain (Note 3)} \\ \text{MMBT2369 (I}_{C} = 10 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc}) \\ \text{MMBT2369A (I}_{C} = 10 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc}) \\ \text{MMBT2369A (I}_{C} = 10 \text{ mAdc, V}_{CE} = 0.35 \text{ Vdc}) \\ \text{MMBT2369A (I}_{C} = 10 \text{ mAdc, V}_{CE} = 0.35 \text{ Vdc}, \\ \text{MMBT2369A (I}_{C} = 30 \text{ mAdc, V}_{CE} = 0.4 \text{ Vdc}) \\ \text{MMBT2369A (I}_{C} = 100 \text{ mAdc, V}_{CE} = 2.0 \text{ Vdc}) \\ \text{MMBT2369A (I}_{C} = 100 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc}) \\ \end{array}$	h _{FE}	40 - 20 30 20 20	- - - - - - -	120 120 - - - - -	_
$\begin{array}{l} \mbox{Collector} - \mbox{Emitter Saturation Voltage (Note 3)} \\ \mbox{MMBT2369} (I_{C} = 10 \mbox{ mAdc}, I_{B} = 1.0 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 10 \mbox{ mAdc}, I_{B} = 1.0 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 10 \mbox{ mAdc}, I_{B} = 1.0 \mbox{ mAdc}, T_{A} = +125^{\circ}\mbox{C}) \\ \mbox{MMBT2369A} (I_{C} = 30 \mbox{ mAdc}, I_{B} = 3.0 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MBT2369A} (I_{C} = 100 \mbox$	V _{CE(sat)}		- - - -	0.25 0.20 0.30 0.25 0.50	Vdc
$ \begin{array}{l} \text{Base} - \text{Emitter Saturation Voltage (Note 3)} \\ \text{MMBT2369/A} \ (I_C = 10 \ \text{mAdc}, \ I_B = 1.0 \ \text{mAdc}) \\ \text{MMBT2369A} \ (I_C = 10 \ \text{mAdc}, \ I_B = 1.0 \ \text{mAdc}, \ T_A = -55^\circ\text{C}) \\ \text{MMBT2369A} \ (I_C = 30 \ \text{mAdc}, \ I_B = 3.0 \ \text{mAdc}) \\ \text{MMBT2369A} \ (I_C = 100 \ \text{mAdc}, \ I_B = 10 \ \text{mAdc}) \\ \end{array} $	V _{BE(sat)}	0.7 _ _ _	- - - -	0.85 1.02 1.15 1.60	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance (V_{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	_	_	4.0	pF
Small Signal CurrentGain (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 100 MHz)	h _{fe}	5.0	_	_	-
SWITCHING CHARACTERISTICS					
Storage Time ($I_{B1} = I_{B2} = I_C = 10 \text{ mAdc}$)	t _s	_	5.0	13	ns
Turn-On Time (V _{CC} = 3.0 Vdc, I _C = 10 mAdc, I _{B1} = 3.0 mAdc)	t _{on}	_	8.0	12	ns
Turn–Off Time (V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = 3.0 mAdc, I_{B2} = 1.5 mAdc)	t _{off}	-	10	18	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.



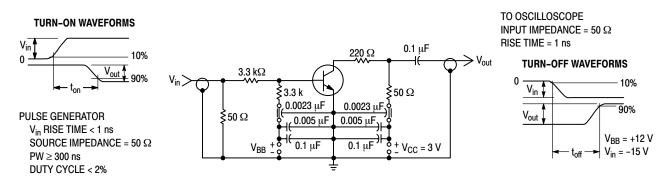


Figure 5. Turn-On and Turn-Off Time Test Circuit

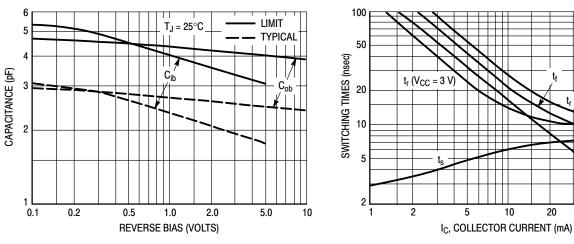


Figure 6. Junction Capacitance Variations



 $\beta_F = 10$

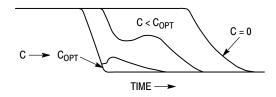
V_{CC} = 10 V

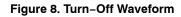
V_{OB} = 2 V

V_{CC} = 10 V

50

100





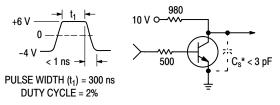
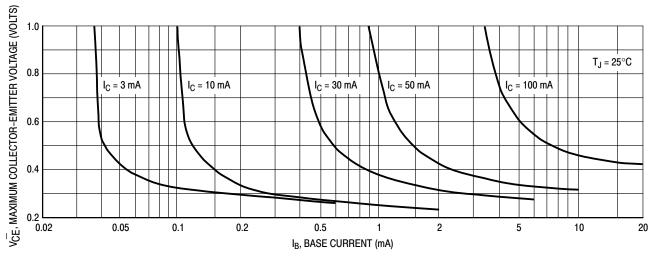


Figure 9. Storage Time Equivalent Test Circuit





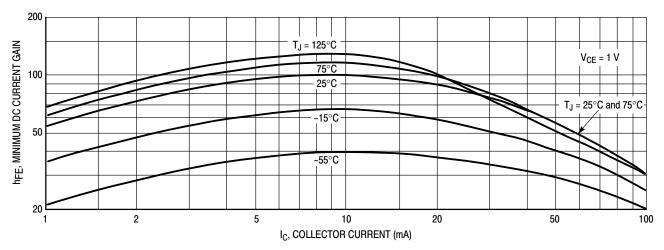


Figure 11. Minimum Current Gain Characteristics

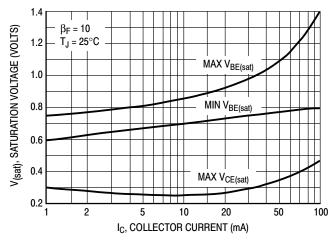


Figure 12. Saturation Voltage Limits

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

D

3

TOP VIEW

SIDE VIEW

Нe

DETAIL A

-3X b

DUSem



SCALE 4:1

Α A1SOT-23 (TO-236) **CASE 318 ISSUE AT**

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DETAIL A

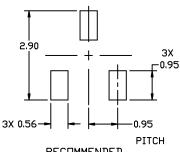
END VIEW

DATE 01 MAR 2023

NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- CONTROLLING DIMENSION: MILLIMETERS 2.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS DF THE BASE MATERIAL. З.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. 4.

	MILLIMETERS			INCHES		
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
с	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
Η _E	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10*	0*		10*



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D. *

GENERIC **MARKING DIAGRAM***



XXX = Specific Device Code

М = Date Code

= Pb-Free Package .

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

onsemi

SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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